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N. Ha
1-16-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Hirotooshi KUBO et al.**

Serial Number: 09/161,828

Art Unit: 2814

Filed: September 29, 1998

Examiner: N. Ha

For: **SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATING THE SAME**

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

November 19, 2001

Sir:

Prior to continued examination on the merits, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Please amend specification as follows:

Please replace the paragraph beginning at page 6, line 11, with the following rewritten paragraph:

As shown in Fig. 1, a first aspect of the present invention is a device of a semiconductor device, which comprises: a semiconductor substrate of a first conduction type; a drain layer of the first conduction type and formed on a surface layer of the semiconductor substrate; a gate insulating film formed in a partial region on the drain layer; a gate electrode formed on the gate insulating film;